

# 1 A Slew Rate Controlled Load Switch with Reverse Blocking

#### **DESCRIPTION**

The SiP32431 is a slew rate controlled high side switch with reverse blocking capability. The switch is of a low ON resistance p-channel MOSFET that supports continuous current up to 1 A.

The SiP32431 operates with an input voltage from 1.5 V to 5.5 V.

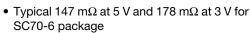
The SiP32431 features low input logic level to interface with low control voltage from microprocessors. This device has a very low operating current, typically 50 pA.

The SiP32431 is available in lead (Pb)-free package options including 6 pin SC70-6, and 4 pin TDFN4 1.2 mm x 1.6 mm DFN4 packages. The operation temperature range is specified from -40  $^{\circ}$ C to +85  $^{\circ}$ C.

The SiP32431 compact package options, operation voltage range, and low operating current make it a good fit for battery power applications.

#### **FEATURES**

- 1.5 V to 5.5 V input voltage range
- Very low  $R_{DS(on)}$ , typically 105 m $\Omega$  at 5 V and 135 m $\Omega$  at 3 V for TDFN4 1.2 mm x 1.6 mm package





- Slew rate controlled turn-on time: 100 µs
- Low quiescent current < 1 μA</li>
- Low shutdown current < 1 μA</li>
- · Reverse blocking capability
- SC70-6 and TDFN4 1.2 mm x 1.6 mm packages
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **APPLICATIONS**

- Cellular telephones
- Digital still cameras
- Personal digital assistants (PDA)
- Hot swap supplies
- Notebook computers
- Personal communication devices
- Portable Instruments

#### TYPICAL APPLICATION CIRCUIT

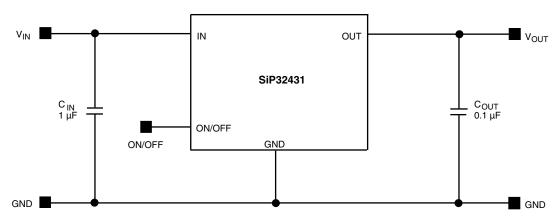


Fig. 1 - SiP32431 Typical Application Circuit

ORDERING INFORMATION						
TEMPERATURE RANGE PACKAGE MARKING PART NUMBER						
-40 °C to 85 °C	SC70-6	MAxx	SiP32431DR3-T1GE3			
-40 C to 65 C	TDFN4 1.2 mm x 1.6 mm	Dx	SiP32431DNP3-T1GE4			

#### **Notes**

- x = lot code
- -GE3 denotes halogen-free and RoHS-compliant
- Please use the SiP32431DR3-T1GE3 to replace SiP32431DR3-T1-E3



www.vishay.com

# Vishay Siliconix

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	LIMIT	UNIT				
Supply Input Voltage (V <sub>IN</sub> )		-0.3 to 6				
Enable Input Voltage (V <sub>ON/OFF</sub> )		-0.3 to 6	V			
Output Voltage (V <sub>OUT</sub> )		-0.3 to V <sub>IN</sub> +0.3				
Maximum Continuous Switch Current (L.)	SC70-6 package	1.2				
Maximum Continuous Switch Current (I <sub>max.</sub> )	TDFN4 1.2 mm x 1.6 mm	1.4				
Maximum Pulsed Current (I <sub>DM</sub> ) V <sub>IN</sub>	$V_{IN} \ge 2.5 \text{ V}$	3	A			
(pulsed at 1 ms, 10 % duty cycle)	V <sub>IN</sub> < 2.5 V	1.6				
ESD Rating (HBM)		4000	V			
Junction Temperature (T <sub>J</sub> )		-40 to 125	°C			
Thermal Desistance (0 ) 3	6 pin SC70-6 <sup>b</sup>	220	°C/W			
Thermal Resistance (θ <sub>JA</sub> ) <sup>a</sup>	4 pin TDFN4 1.2 mm x 1.6 mm <sup>c</sup>	170	C/W			
Device Dissipation (D.) 3	6 pin SC70- 6 <sup>b</sup>	250	\/			
Power Dissipation (P <sub>D</sub> ) <sup>a</sup>	4 pin TDFN4 1.2 mm x 1.6 mm <sup>c</sup>	324	mW			

#### Notes

- a. Device mounted with all leads and power pad soldered or welded to PC board.
- b. Derate 4.5 mW/°C above  $T_A = 70$  °C.
- c. Derate 5.9 mW/°C above  $T_A = 70$  °C, see PCB layout.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating/conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE					
PARAMETER	LIMIT	UNIT			
Input Voltage Range (V <sub>IN</sub> )	1.5 to 5.5	V			
Operating Temperature Range	-40 to 85	°C			



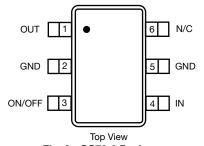
# Vishay Siliconix

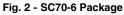
SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS SPECIFIED $V_{IN} = 5, T_A = -40 \text{ °C to } 85 \text{ °C}$		LIMITS -40 °C TO 85 °C			UNIT
		(Typical values are at T <sub>A</sub> = 25 °	°C)	MIN. a	TYP. b	MAX. a	
Operating Voltage <sup>c</sup>	V <sub>IN</sub>			1.5	-	5.5	V
Quiescent Current	ΙQ	On/off = active		-	0.00005	1	
Off Supply Current	I <sub>Q(off)</sub>	On/off = inactive, out = oper	١	-	-	1	μA
Off Switch Current	I <sub>SD(off)</sub>	On/off = inactive, out = 0		-	-	1	μΑ
Reverse Blocking Current	I <sub>RB</sub>	$V_{OUT} = 5.5 \text{ V}, V_{IN} = 0, V_{on/off} = ina$	ctive	-	0.13	1	
		V 5 V 1 500 m A T 25 °C	SC70-6	-	147	000	
		$V_{IN} = 5 \text{ V}, I_L = 500 \text{ mA}, T_A = 25 \text{ °C}$	TDFN4	-	105	230	
		V 40VI 500 mA T 25 °C	SC70-6	-	155	050	
	R <sub>DS(on)</sub>	$V_{IN} = 4.2 \text{ V}, I_L = 500 \text{ mA}, T_A = 25 \text{ °C}$	TDFN4	-	110	250	mΩ
On Besistance		V <sub>IN</sub> = 3 V, I <sub>L</sub> = 500 mA, T <sub>A</sub> = 25 °C	SC70-6	-	178	290	
On-Resistance			TDFN4	-	135		
		V <sub>IN</sub> = 1.8 V, I <sub>L</sub> = 500 mA, T <sub>A</sub> = 25 °C	SC70-6	-	275	480	
			TDFN4	-	230		
		V 45V L 500 × A T 05 00	SC70-6	-	395	520	
		$V_{IN} = 1.5 \text{ V}, I_L = 500 \text{ mA}, T_A = 25 \text{ °C}$	TDFN4	-	350		
On-Resistance TempCoefficient	TD <sub>RDS</sub>			-	2800	-	ppm/°C
		V <sub>IN</sub> ≥ 1.5 V to < 1.8 V		-	-	0.3	
On/Off Input Low Voltage <sup>c</sup>	$V_{IL}$	V <sub>IN</sub> ≥ 1.8 V to < 2.7 V		-	-	0.4	
		$V_{IN} \ge 2.7 \text{ V to} \le 5.5 \text{ V}$		-	-	0.6	V
		V <sub>IN</sub> ≥ 1.5 V to < 2.7 V		1.3	-	-	ľ
On/Off Input Low Voltage c	$V_{IH}$	V <sub>IN</sub> ≥ 2.7 V to < 4.2 V		1.5	-	-	
		$V_{IN} \ge 4.2 \text{ V to} \le 5.5 \text{ V}$		1.8	-	-	
On/Off Input Leakage	I <sub>SINK</sub>	$V_{On/Off} = 5.5 \text{ V}$		-	-	1	μΑ
Output Turn-On Delay Time	t <sub>d(on)</sub>			-	20	40	
Output Turn-On Rise Time	t <sub>(on)</sub>	$V_{IN} = 5 \text{ V}, R_{load} = 10 \Omega, T_A = 25$	°C	ı	140	180	μs
Output Turn-Off Delay Time	t <sub>d(off)</sub>			-	4	10	1

#### Notes

- a. The algebriac convention whereby the most negative value is a minimum and the most positive a maximum.
- b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- c. For  $V_{\mbox{\scriptsize IN}}$  outside this range consult typical on/off threshold curve.

#### **PIN CONFIGURATION**





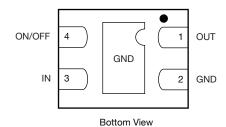


Fig. 3 - TDFN4 1.2 mm x 1.6 mm Package

PIN DES	PIN DESCRIPTION					
PIN NUMBER		NAME	FUNCTION			
SC70-6	TDFN4	INAIVIE	FUNCTION			
4	3	IN	This pin is the p-channel MOSFET source connection. Bypass to ground through a 1 µF capacitor			
2, 5	2	GND	Ground connection			
3	4	ON/OFF	Enable input			
1	1	OUT	This pin is the p-channel MOSFET drain connection. Bypass to ground through a 0.1 µF capacitor			



#### TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

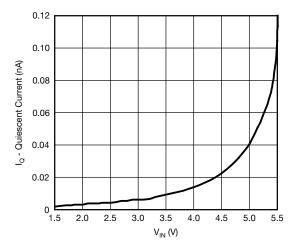


Fig. 4 - Quiescent Current vs. Input Voltage

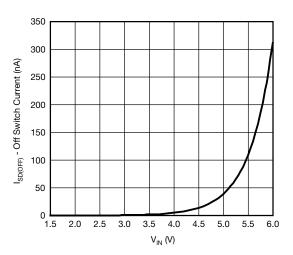


Fig. 5 - Off Switch Current vs. Input Voltage

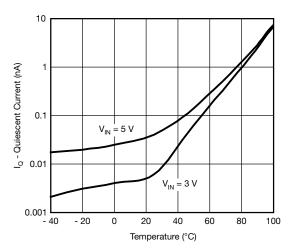


Fig. 6 - Quiescent Current vs. Temperature

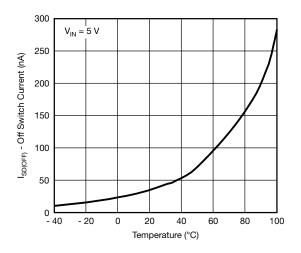


Fig. 7 - Off Switch Current vs. Temperature

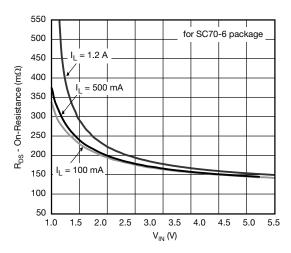


Fig. 8 - R<sub>DS(on)</sub> vs. V<sub>IN</sub> for SC70-6 Package

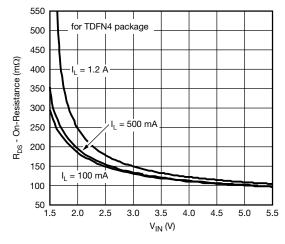


Fig. 9 - R<sub>DS(on)</sub> vs. Input Voltage



#### TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

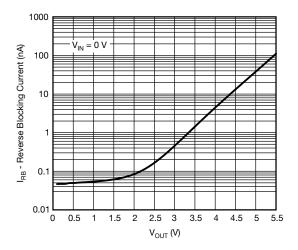


Fig. 10 - Reverse Blocking Current vs. Vout

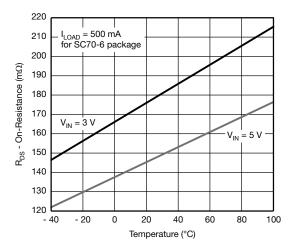


Fig. 11 - R<sub>DS(on)</sub> vs. Temperature

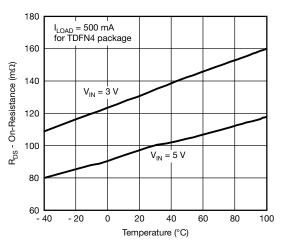


Fig. 12 - R<sub>DS(on)</sub> vs. Temperature

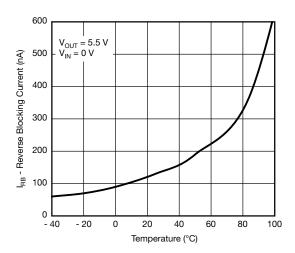


Fig. 13 - Reverse Blocking Current vs. Temperature

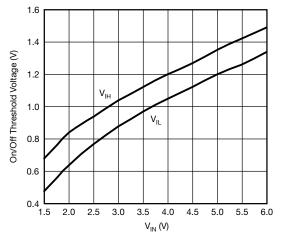
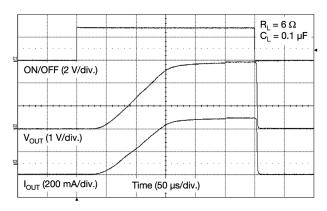


Fig. 14 - On/Off Threshold vs. Input Voltage

ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



#### **TYPICAL WAVEFORMS**





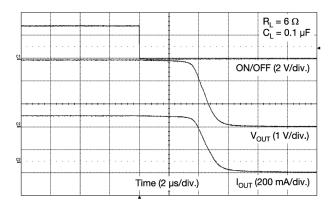


Fig. 17 - Turn-Off (V<sub>IN</sub> = 3 V)

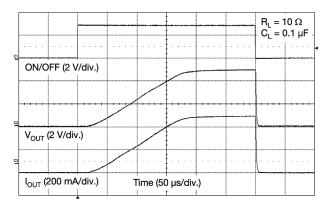


Fig. 16 - Switching (V<sub>IN</sub> = 5 V)

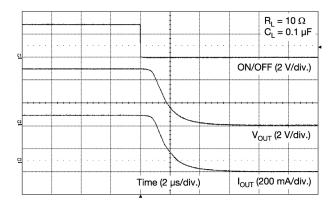


Fig. 18 - Turn-Off ( $V_{IN} = 5 V$ )

#### **BLOCK DIAGRAM**

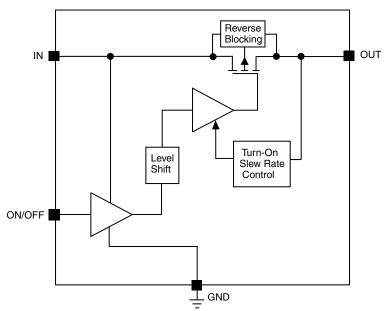


Fig. 19 - Functional Block Diagram

#### **PCB LAYOUT**

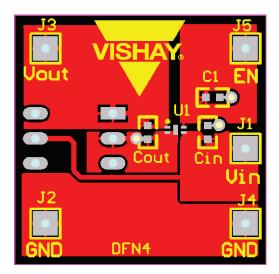


Fig. 20 - Top, TDFN4 1.2 mm x 1.6 mm PCB Layout

#### **DETAILED DESCRIPTION**

The SiP32431 is a p-channel MOSFET power switches designed for high-side slew rate controlled load-switching applications. Once turned on, the slew-rate control circuitry is activated and current is ramped in a linear fashion until it reaches the level required for the output load condition. This is accomplished by first elevating the gate voltage of the MOSFET up to its threshold voltage and then by linearly increasing the gate voltage until the MOSFET becomes fully enhanced. At this point, the gate voltage is then quickly increased to the full input voltage to reduce R<sub>DS(on)</sub> of the MOSFET switch and minimize any associated power losses.

#### **APPLICATION INFORMATION**

#### **Input Capacitor**

While a bypass capacitor on the input is not required, a 1  $\mu$ F or larger capacitor for C<sub>IN</sub> is recommended in almost all applications. The bypass capacitor should be placed as physically close as possible to the SiP32431 to be effective in minimizing transients on the input. Ceramic capacitors are recommended over tantalum because of their ability to withstand input current surges from low impedance sources such as batteries in portable devices.

#### **Output Capacitor**

A 0.1  $\mu$ F capacitor or larger across  $V_{OUT}$  and GND is recommended to insure proper slew operation.  $C_{OUT}$  may be increased without limit to accommodate any load transient condition with only minimal affect on the SiP32431 turn on slew rate time. There are no ESR or capacitor type requirement.

#### **Enable**

The on/off pin is compatible with both TTL and CMOS logic voltage levels.

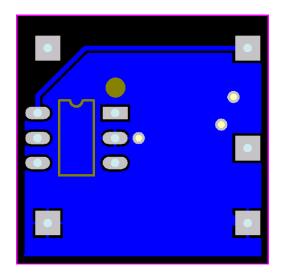


Fig. 21 - Bottom, TDFN4 1.2 mm x 1.6 mm PCB Layout

#### **Protection Against Reverse Voltage Condition**

The SiP32431 contains a body snatcher that normally connect the body to the source (IN) when the device is enable. In case where the device is disabled but the  $V_{OUT}$  is higher than the  $V_{IN}$ , the n-type body is switched to OUT, reverse bias the body diode to prevent the current from going back to the input.

#### Thermal Considerations

The SiP32431 is designed to maintain a constant output load current. Due to physical limitations of the layout and assembly of the device the maximum switch current is 1 A, as stated in the Absolute Maximum Ratings table. However, another limiting characteristic for the safe operating load current is the thermal power dissipation of the package. To obtain the highest power dissipation (and a thermal resistance of 170 °C/W) the power pad of the device should be connected to a heat sink on the printed circuit board.

The maximum power dissipation in any application is dependent on the maximum junction temperature,  $T_{J\,(max.)}$  = 125 °C, the junction-to-ambient thermal resistance for the TDFN4 1.2 mm x 1.6 mm package,  $\theta_{J-A}$  = 170 °C/W, and the ambient temperature,  $T_A$ , which may be formulaically expressed as:

$$P \text{ (max.)} = \frac{T_{J \text{ (max.)}} - T_{A}}{\theta_{J - A}} = \frac{125 - T_{A}}{170}$$

It then follows that, assuming an ambient temperature of 70 °C, the maximum power dissipation will be limited to about 324 mW.

So long as the load current is below the 1 A limit, the maximum continuous switch current becomes a function two things: the package power dissipation and the  $R_{DS(on)}$  at the ambient temperature.





www.vishay.com

Vishay Siliconix

As an example let us calculate the worst case maximum load current at  $T_A=70~^{\circ}\text{C}$ . The worst case  $R_{DS(\text{on})}$  at 25  $^{\circ}\text{C}$  occurs at an input voltage of 1.5 V and is equal to 520 m $\Omega$ . The  $R_{DS(\text{on})}$  at 70  $^{\circ}\text{C}$  can be extrapolated from this data using the following formula

$$R_{DS(on)}$$
 (at 70 °C) =  $R_{DS(on)}$  (at 25 °C) x (1 +  $T_C$  x  $\Delta T$ )

Where  $T_C$  is 3300 ppm/°C. Continuing with the calculation we have

 $R_{DS(on)}$  (at 70 °C) = 520 m $\Omega$  x (1 + 0.0033 x (70 °C - 25 °C)) = 597 m $\Omega$ 

The maximum current limit is then determined by

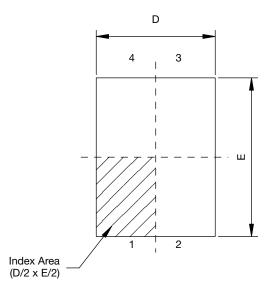
$$I_{LOAD (max.)} < \sqrt{\frac{P (max.)}{R_{DS(on)}}}$$

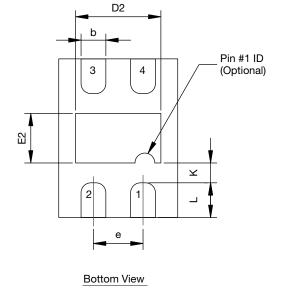
which in case is 0.74 A. Under the stated input voltage condition, if the 0.74 A current limit is exceeded the internal die temperature will rise and eventually, possibly damage the device.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?66597">www.vishay.com/ppg?66597</a>.

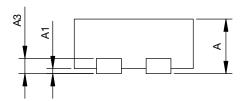


## TDFN4 1.2 x 1.6 Case Outline





Top View



Side View

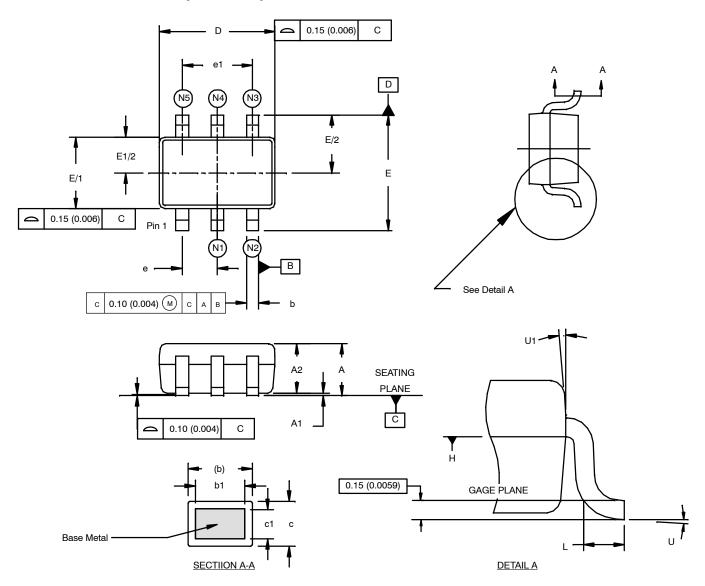
DIM.		MILLIMETERS			INCHES	3	
DIN.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.45	0.55	0.60	0.017	0.022	0.024	
A1	0.00	-	0.05	0.00	-	0.002	
A3	0.	15 REF. or 0.127 REF	. (1)		0.006 or 0.005 <sup>(1)</sup>		
b	0.20	0.25	0.30	0.008	0.010	0.012	
D	1.15	1.20	1.25	0.045	0.047	0.049	
D2	0.81	0.86	0.91	0.032	0.034	0.036	
е		0.50 BSC			0.020		
Е	1.55	1.60	1.65	0.061	0.063	0.065	
E2	0.45	0.50	0.55	0.018	0.020	0.022	
K		0.25 typ.			0.010 typ.		
L	0.25	0.30	0.35	0.010	0.012	0.014	

#### Note

<sup>(1)</sup> The dimension depends on the leadframe that assembly house used.



#### SC-70: 3/4/5/6-LEADS (PIC ONLY)



Pin	LEAD COUNT					
Code	3	4	5	6		
N1	-	_	2	2		
N2	2	2	3	3		
N3	-	3	4	4		
N4	3	_	-	5		
N5	-	4	5	6		

#### NOTES:

- 1. Dimensioning and tolerancing per ANSI Y14.5M-1994.
- 2. Controlling dimensions: millimeters converted to inch dimensions are not necessarily exact.
- Dimension "D" does not include mold flash, protrusion or gate burr. Mold flash, protrusion or gate burr shall not exceed 0.15 mm (0.006 inch) per side.
- 4. The package top shall be smaller than the package bottom. Dimension "D" and "E1" are determined at the outer most extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.

# Vishay Siliconix



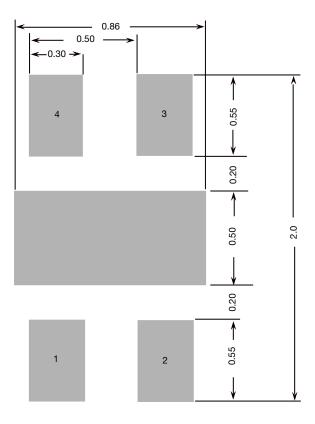
	MILLIMETERS INCHES						
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.80	_	1.10	0.031	-	0.043	
A1	0.00	-	0.10	0.000	-	0.004	
A2	0.80	0.90	1.00	0.031	0.035	0.040	
b	0.15	_	0.30	0.006	-	0.012	
b1	0.15	0.20	0.25	0.006	0.008	0.010	
С	0.08	-	0.25	0.003	-	0.010	
с1	0.08	0.13	0.20	0.003	0.005	0.008	
D	1.90	2.10	2.15	0.074	0.082	0.084	
E	2.00	2.10	2.20	0.078	0.082	0.086	
E <sub>1</sub>	1.15	1.25	1.35	0.045	0.050	0.055	
е		0.65 BSC			0.0255 BSC		
e <sub>1</sub>	1.30 BSC				0.0512 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018	
U	0°	-	8°	0°	-	8°	
U1	4°		10°	4°		10°	
ECN: S-42145—Rev. A, 22-Nov-04 DWG: 5941							

www.vishay.com Document Number: 73201 2 19-Nov-04



Vishay Siliconix

#### **RECOMMENDED MINIMUM PADS FOR TDFN4 1.2 x 1.6**



Recommended Minimum Pads Dimensions in mm



## **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

# Vishay:

SIP32431DNP3-T1GE4 SIP32431DR3-T1GE3 SiP32430EVB